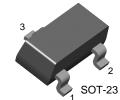


November 2006

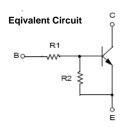
# FJV3114R NPN Epitaxial Silicon Transistor

### **Features**

- · Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R1=4.7KΩ, R2=47KΩ)
- Complement to FJV4114R







1. Base 2. Emitter 3. Collector

## Absolute Maximum Ratings \* T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
I <sub>C</sub>	Collector Current	100	mA
T <sub>STG</sub>	Storage Temperature Range	-55~150	°C
T <sub>J</sub>	Junction Temperature	150	°C
P <sub>C</sub>	Collector Power Dissipation, by $R_{\theta JA}$	200	mW

С

## Electrical Characteristics\* T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	MIN	Тур	MAX	Units
V <sub>(BR)</sub> CBO	Collector-Emitter Breakdown Voltage	Ic= 10 uA, IE= 0	50			V
V <sub>(BR)</sub> CEO	Collector-Base Breakdown Voltage	Ic = 100 uA, IB = 0	50			V
Ісво	Collector-Cutoff Current	Vcb = 40 V, IE = 0			0.1	uA
hfE	DC Current Gain	Vce = 5 V, Ic = 5 mA	68			
Vce(sat)	Collector-Emitter Saturation Voltage	Ic= 10 mA, Iв= 0.5 mA			0.3	V
f⊤	Current Gain - Bandwidth Product	VcE = 10V, Ic = 5 mA		250		MHz
Ccb	Output Capacitance	Vcb = 10 V, IE = 0, f = 1.0 MHz		3.7		pF
Vı(off)	Input Off Voltage	VcE = 5 V, Ic = 100uA	0.5			V
Vı(on)	Input On Voltage	Vce = 0.2V, Ic = 5mA			1.3	V
R <sub>1</sub>	Input Resistor		3.2	4.7	6.2	ΚΩ
R <sub>1</sub> /R <sub>2</sub>	Resistor Ratio		0.09	0.1	0.11	

<sup>\*</sup> Pulse Test: PW≤300µs, Duty Cycle≤2%

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may by impaired.

## **Typical Performance Characteristics**

Figure 1. DC current Gain

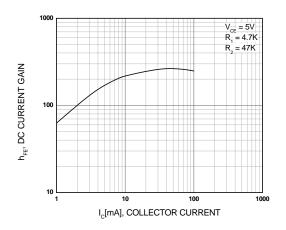


Figure 2. Input On Voltage

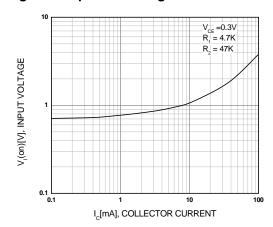


Figure 3. Collector-Emitter Saturation Voltage

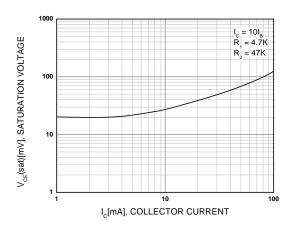
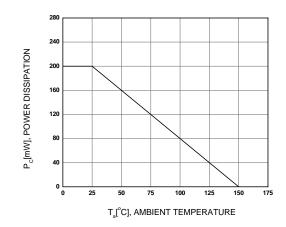
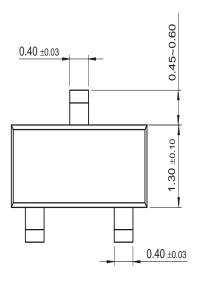


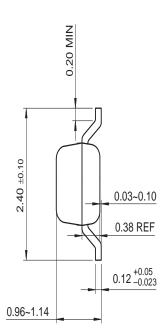
Figure 4. Power Derating

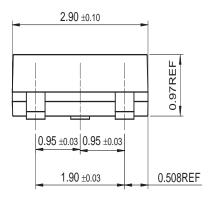


# **Package Dimensions**

# **SOT-23**







Dimensions in Millimeters

UltraFET®

UniFET™

 $VCX^{TM}$ 

Wire™



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The Power Franchise<sup>®</sup> ScalarPump™ UHC<sup>®</sup>

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Rev. I21